## Amitabh Chatterjee

List of Publications by Year in descending order

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1163117 1281871 22 144 8 11 citations g-index h-index papers 22 22 22 141 docs citations times ranked citing authors all docs

#	Article	IF	Citations
1	Circuit modeling and performance analysis of photoconductive antenna. Optics Communications, 2017, 394, 69-79.	2.1	25
2	The principle of operation of the avalanche transistor-based Marx bank circuit: A new perspective. Review of Scientific Instruments, 1998, 69, 2166-2170.	1.3	21
3	A High Precision Lumped Parameter Model for Piezoelectric Energy Harvesters. IEEE Sensors Journal, 2017, 17, 8350-8355.	4.7	15
4	An Insight Into the ESD Behavior of the Nanometer-Scale Drain-Extended NMOS Deviceâ€"Part I: Turn-On Behavior of the Parasitic Bipolar. IEEE Transactions on Electron Devices, 2011, 58, 309-317.	3.0	12
5	Breakdown of transistors in Marx bank circuit. Solid-State Electronics, 2000, 44, 1679-1684.	1.4	11
6	2-D Analytical Modeling of Surface Potential and Threshold Voltage for Vertical Super-Thin Body FET. IEEE Transactions on Electron Devices, 2017, 64, 2106-2112.	3.0	11
7	Mechanisms leading to erratic snapback behavior in bipolar junction transistors with base emitter shorted. Journal of Applied Physics, 2005, 97, 084504.	2.5	10
8	Magnetic Field-Assisted Radiation Enhancement From a Large Aperture Photoconductive Antenna. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 678-687.	4.6	9
9	An Insight into the High Current ESD Behavior of Drain Extended NMOS (DENMOS) Devices in Nanometer Scale CMOS Technologies. , 2007, , .		8
10	An Insight Into ESD Behavior of Nanometer-Scale Drain Extended NMOS (DeNMOS) Devices: Part II (Two-Dimensional Study-Biasing & Ecomparison With NMOS). IEEE Transactions on Electron Devices, 2011, 58, 318-326.	3.0	7
11	Time dependent capacitance in Photoconductive Antenna., 2015,,.		4
12	Modeling Erratic Behavior Due to High Current Filamentation in Bipolar Structures Under Dynamic Avalanche Conditions. IEEE Transactions on Electron Devices, 2016, , 1-8.	3.0	4
13	Effect of near fields on radiation from photoconductive antenna. , 2017, , .		2
14	Design of band-gap engineered silicon-germanium Junctionless Double-gate FET for ZRAM application. , 2015, , .		1
15	Methodology for optimizing ESD protection for high speed LVDS based I/Os. , 2015, , .		1
16	A Novel Co-design Methodology for Optimizing ESD Protection Device Using Layout Level Approach., 2016,,.		1
17	SPICE level implementation of physics of filamentation in ESD protection devices. Microelectronics Reliability, 2017, 79, 239-247.	1.7	1
18	Fast Ionization-Front-Induced Anomalous Switching Behavior in Trigger Bipolar Transistors of Marx-Bank Circuits Under Base-Drive Conditions. IEEE Transactions on Plasma Science, 2018, 46, 2064-2071.	1.3	1

#	Article	IF	CITATIONS
19	A parametric study of photo carrier generation in Photoconductive Antenna. , 2015, , .		O
20	A Novel Capacitorless DRAM Cell Design Using Band-Gap Engineered Junctionless Double-Gate FET. , 2016, , .		0
21	Equivalent electrical circuit model of Terahertz photoconductive antenna receiver in a pulsed system. , 2017, , .		O
22	Bipolar effects in snapback mechanism in advanced n-FET transistors under high current stress conditions. Journal of Physics Communications, 2020, 4, 065009.	1.2	0